

**ABSTRACT**

A method for forming in monolithic form a DRAM-type memory, including the steps of forming, on a substrate, parallel strips including a lower insulating layer, a strongly-conductive layer, a single-crystal semiconductor layer, and an upper insulating layer; digging, perpendicularly to the strips, into the upper insulating layer and into a portion of the semiconductor layer, first and second parallel trenches, each first and second trench being shared by neighboring cells; forming, in each first trench, a first conductive line according to the strip width; forming, in each second trench, two second distinct parallel conductive lines, insulated from the peripheral layers; filling the first and second trenches with an insulating material; removing the remaining portions of the upper insulating layer; and depositing a conductive layer.